



NTDV3055L104-1G Information



For Reference Only

Part Number NTDV3055L104-1G
Manufacturer ON Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 60V 12A IPAK

Package TO-251-3 Short Leads, IPak, TO-251AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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NTDV3055L104-1G Specifications

Manufacturer Part Number NTDV3055L104-1G Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-251-3 Short Leads, IPak, TO-251AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 12A (Ta) Drive Voltage (Max Rds On, Min Rds On) 5V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 20nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 440pF @ 25V Vgs (Max) ±15V FET Feature - Power Dissipation (Max) 1.5W (Ta), 48W (Tj) Rds On (Max) @ Id, Vgs 104 mOhm @ 6A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA		
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PackageTO-251-3 Short Leads, IPak, TO-251AASeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C12A (Ta)Drive Voltage (Max Rds On, Min Rds On)5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs20nC @ 5VInput Capacitance (Ciss) (Max) @ Vds440pF @ 25VVgs (Max)±15VFET Feature-Power Dissipation (Max)1.5W (Ta), 48W (Tj)Rds On (Max) @ Id, Vgs104 mOhm @ 6A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Category	Discrete Semiconductor Products
Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 12A (Ta) Drive Voltage (Max Rds On, Min Rds On) 5V Vgs(th) (Max) @ Id 2V @ 250μA Gate Charge (Qg) (Max) @ Vgs 20nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 440pF @ 25V Vgs (Max) ±15V FET Feature - Power Dissipation (Max) 1.5W (Ta), 48W (Tj) Rds On (Max) @ Id, Vgs 104 mOhm @ 6A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C12A (Ta)Drive Voltage (Max Rds On, Min Rds On)5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs20nC @ 5VInput Capacitance (Ciss) (Max) @ Vds440pF @ 25VVgs (Max)±15VFET Feature-Power Dissipation (Max)1.5W (Ta), 48W (Tj)Rds On (Max) @ Id, Vgs104 mOhm @ 6A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Package	TO-251-3 Short Leads, IPak, TO-251AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C12A (Ta)Drive Voltage (Max Rds On, Min Rds On)5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs20nC @ 5VInput Capacitance (Ciss) (Max) @ Vds440pF @ 25VVgs (Max)±15VFET Feature-Power Dissipation (Max)1.5W (Ta), 48W (Tj)Rds On (Max) @ Id, Vgs104 mOhm @ 6A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Series	-
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C12A (Ta)Drive Voltage (Max Rds On, Min Rds On)5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs20nC @ 5VInput Capacitance (Ciss) (Max) @ Vds440pF @ 25VVgs (Max)±15VFET Feature-Power Dissipation (Max)1.5W (Ta), 48W (Tj)Rds On (Max) @ Id, Vgs104 mOhm @ 6A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.5W (Ta), 48W (Tj) Rds On (Max) @ Id, Vgs 104 mOhm @ 6A, 5V Operating Temperature Supplier Device Package Package / Case 12A (Ta) 14A (Ta) 14A (Ta) 15V FET Feature -5V Though Hole 1-Pak To-251-3 Short Leads, IPak, TO-251AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs20nC @ 5VInput Capacitance (Ciss) (Max) @ Vds440pF @ 25VVgs (Max)±15VFET Feature-Power Dissipation (Max)1.5W (Ta), 48W (Tj)Rds On (Max) @ Id, Vgs104 mOhm @ 6A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Through Hole Supplier Device Package Package / Case 20nC @ 5V 440pF @ 25V 4	Current - Continuous Drain (Id) @ 25°C	12A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 440pF @ 25V Vgs (Max) ±15V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 104 mOhm @ 6A, 5V Operating Temperature -5°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Drive Voltage (Max Rds On, Min Rds On)	5V
Input Capacitance (Ciss) (Max) @ Vds 440pF @ 25V Vgs (Max) ±15V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.5W (Ta), 48W (Tj) Rds On (Max) @ Id, Vgs 104 mOhm @ 6A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs(th) (Max) @ Id	2V @ 250μA
Vgs (Max) ±15V FET Feature - Power Dissipation (Max) 1.5W (Ta), 48W (Tj) Rds On (Max) @ Id, Vgs 104 mOhm @ 6A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Gate Charge (Qg) (Max) @ Vgs	20nC @ 5V
FET Feature - Power Dissipation (Max) 1.5W (Ta), 48W (Tj) Rds On (Max) @ Id, Vgs 104 mOhm @ 6A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Input Capacitance (Ciss) (Max) @ Vds	440pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 104 mOhm @ 6A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs (Max)	±15V
Rds On (Max) @ Id, Vgs104 mOhm @ 6A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Power Dissipation (Max)	1.5W (Ta), 48W (Tj)
Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Rds On (Max) @ Id, Vgs	104 mOhm @ 6A, 5V
Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Mounting Type	Through Hole
	Supplier Device Package	I-Pak
Report errors?	Package / Case	TO-251-3 Short Leads, IPak, TO-251AA
		Report errors?

NTDV3055L104-1G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

NTDV3055L104-1G Payment Methods



















NTDV3055L104-1G Shipping Methods













If you have any question about NTDV3055L104-1G, please do not hesitate to contact us!

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